### BE (Third Semester)

Information Technology Basic Electronics & Network Theory - 333353(33) 2015 - Summer Session , New Scheme

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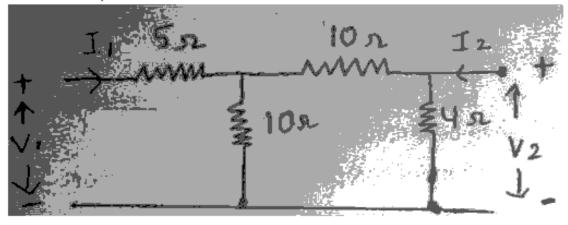
## Chapter 1

Define Thevenin's theorem.

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2 Find the z-parameter of the network shown.

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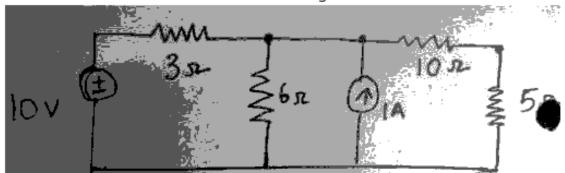


3 State and prove maximum power transfer theorem.

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4 Find the current in 5 Ω Resistor using Norton's theorem.

7



# Chapter 2

What is an Ideal Diode.

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- 2 Define transition capacitance of a P-N junction diode and obtain 7 the expression for transition capacitance.
- 3 Explain the working of full wave rectifier and find the expression 7 for its transformer utilization factor (TUF).
- 4 Draw the circuit diagram of capacitor filter and explain its 7 working.

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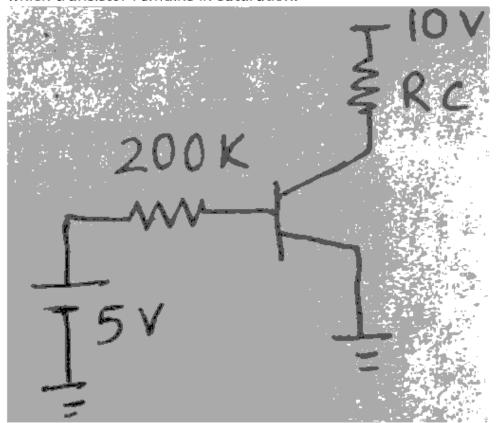
### Chapter 3

- 1 Why base is lightly doped?
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- 2 Draw and explain output characteristics of common base 7 configuration.
- 3 Explain current component in PNP transistor.

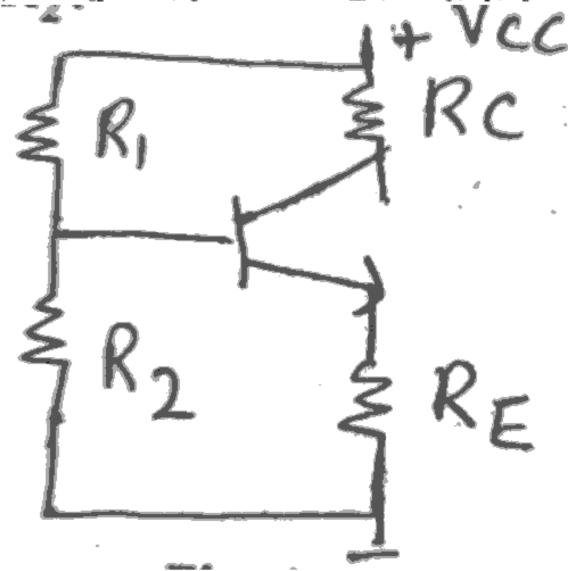
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- A silicon transistor with  $V_{BESat} = 0.8 \text{ V}$ ,  $\Omega = 100$ ,  $V_{Ce_{sat}} = 0.2 \text{ is}$  used in the circuit shown. Find the minimum value of  $\Omega$  for which transistor remains in saturation.



# Chapter 4 CSVTUonline.com

- 1 List the three sources of instability of collector current.
- 2
- 2 Draw the circuit diagram of CE amplifier with diode compensation 7 for I<sub>CO</sub>.

- 3 Draw and explain the working of collector to base bias and find 7 the expression for stability factor S.
- 4 For a silicon transistor with ß = 50,  $V_{BE}$  = 0.7,  $V_{CC}$  = 22.5 V and  $R_C$  = 5.6 K is used in the fig shown it is desired to establish Q point at  $V_{CE}$  = 12 V,  $I_C$  = 1.5 mA and  $S \le 3$ , find  $R_e$ ,  $R_1$ ,  $R_2$ .



Chapter 5

2

- Give the comparison of BJT with FET.
- 2 Draw and explain drain characteristics and transfer characteristic 7 of JFET.
- 3 Explain the working of enhancement MOSFET.
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